

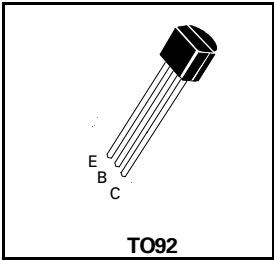
NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTOR

BC372

ISSUE 2 – SEPT 93

FEATURES

- * 100 Volt V_{CE0}
- * Gain of 8k at $I_C=250\text{mA}$
- * $I_C=1\text{Amp}$



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	12	V
Continuous Collector Current	I_C	1	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	625	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100			V	$I_C=100\mu\text{A}$, $I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	100			V	$I_C=100\mu\text{A}$, $I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	12			V	$I_E=10\mu\text{A}$, $I_C=0$
Collector Cut-Off Current	I_{CBO}			100	nA	$V_{CB}=80\text{V}$, $I_E=0$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB}=10\text{V}$, $I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1.0	V	$I_C=250\text{mA}$, $I_B=0.25\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			2	V	$I_C=250\text{mA}$, $I_B=0.25\text{mA}$
Static Forward Current Transfer Ratio	h_{FE}	10K 8K				$I_C=100\text{mA}$, $V_{CE}=5\text{V}^*$ $I_C=250\text{mA}$, $V_{CE}=5\text{V}^*$
Transition Frequency	f_T	100			MHz	$I_C=100\text{mA}$, $V_{CE}=5\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}			25	pF	$V_{CB}=10\text{V}$, $f=1\text{MHz}$

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